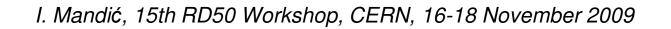
## Recent results of measurements of annealing effects in irradiated Hamamatsu p-type microstrip detector with SCT128 chip

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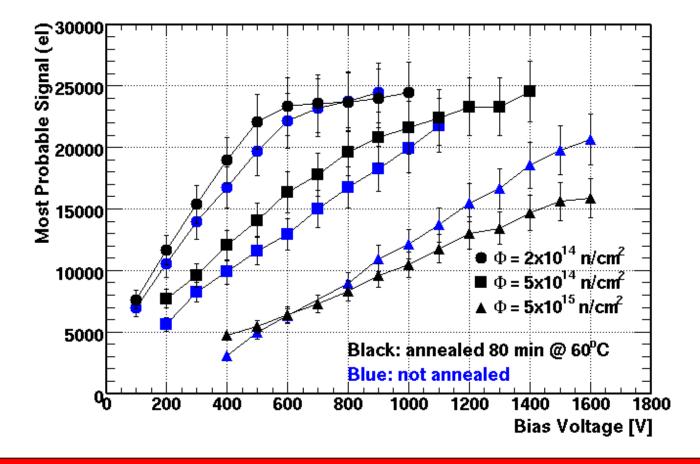
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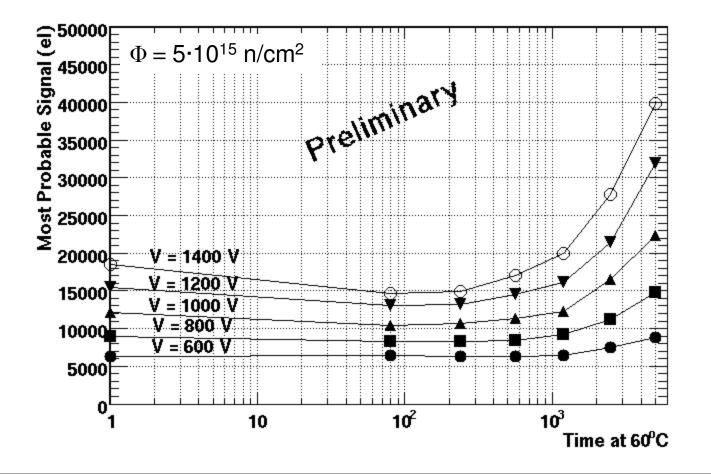


- miniature microsctrip Hamamatsu detectors from ATLAS strip upgrade project
- FZ, p-type, 320 μm thick, 75 μm pitch, 1x1 cm2 (ATLAS07A, Z3, W44)
- detectors irradiated with neutrons in Ljubljana reactor
- signals from <sup>90</sup>Sr electrons measured with SCT128 chip



more annealing steps with detector irradiated to 5.10<sup>15</sup> n/cm<sup>2</sup>

→ large rise of collected charge with annealing time at high bias voltage



noise increases with annealing time

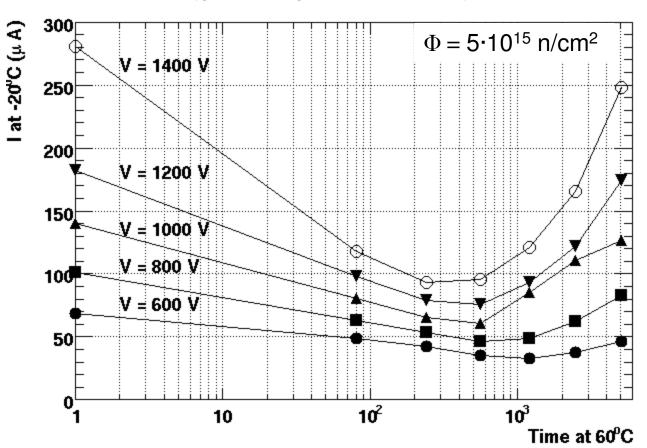
Signal/Noise: Noise: 3000 Noise (el) 25 Signal/Noise preliminary  $\Phi = 5.10^{15} \text{ n/cm}^2$  $\Phi = 5.10^{15} \text{ n/cm}^2$ 2500 20 V = 1400 V = 1200 V 2000 V = 1400 V = 1000 V V = 800 V V = 1200 V 1500 V = 600 V V = 1000 V V = 800 V 10 1000 V = 600 V 500 0' 1 10<sup>2</sup> 10<sup>3</sup> 10 1 10<sup>2</sup> 10<sup>3</sup> 10 Time at 60°C Time at 60°C

ratio signal/noise constant

•••



- leakage current
  - → large increase of current with annealing time at high bias voltage
  - → increase of noise larger than expected from increase of leakage current



Current (guard ring not connected) at -20° C

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## Conclusions

- unusual annealing behavior measured with detector irradiated to 5.10<sup>15</sup> n/cm<sup>2</sup>
- it looks as if multiplication effects amplify with annealing:
  - measured charge increases
  - current increases
- measurements with different method on different detector confirm the hypothesis
  measurements on Micron detector with Edge-TCT presented by Marko

Future work:

• confirm measurements with another detector with new SCT128 chip



